

ABSTRACT OF THE DISCLOSURE

A conductor film and a cap insulating film are sequentially formed, and a laminated film constituted of the cap insulating film and the conductor film is patterned, and then a gate electrode is formed. Next, source and drain diffusion regions are formed, and a first silicon nitride film is formed on a sidewall of the laminated film, and then a second silicon nitride film is formed on an entire surface, and further a silicon oxide film is deposited. Next, the silicon oxide film is left between the gate electrodes, and the second silicon nitride film on the laminated film is removed, and the cap insulating film left above the gate electrode is removed, and a metal silicide film is formed on a surface of the gate electrode, and then a third silicon nitride film is left on the gate electrode.